CLAIMS

[1] A protection film for a thin film device formed on a substrate, which is characterized by having a hydrogen content of not less than 30 at%.

[2] A protection film according to Claim 1, wherein the protection film is one of SiN, SiO, SiON, SiC or SiCN type or diamond like carbon (DLC).

[3] An organic electroluminescent device which comprises at least a first electrode, an organic luminescent layer, and a second electrode formed on a substrate, which is characterized by forming a protection film which covers the organic electroluminescent device and of which hydrogen content is not less than 30at%

[4] An organic electroluminescent device according to Claim 3, wherein the protection film is one of SiN, SiO, SiON, SiC or SiCN type or diamond like carbon (DLC).

[5] A process for manufacturing an organic electroluminescent device which comprises at least a first electrode, an organic luminescent layer, and an second electrode formed on a substrate, which is characterized by forming a protection film which covers the organic

electroluminescent device and of which hydrogen content is not less than 30at% through the use of CVD method or spattering method.

[6] A process according to Claim 5, wherein the CVD method is plasma CVD method.